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FGH75T65UPD_F085 650V, 75A Field Stop Trench IGBT

Features

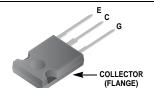
- Maximum Junction Temperature : T_J = 175°C
- Positive Temperaure Co-efficient for easy parallel operating
- · High current capability
- Low saturation voltage: $V_{CE(sat)} = 1.65V(Typ.)$ @ $I_C = 75A$
- · High input impedance
- Tightened Parameter Distribution
- · RoHS compliant
- Qualified to Automotive Requirements of AEC-Q101



Using Novel Field Stop Trench IGBT Technology, Fairchild's new series of Field Stop Trench IGBTs offer the optimum performance for Automotive chargers, Solar Inverter, UPS and Digital Power Generator where low conduction and switching losses are essential.

Applications

- Automotive chargers, Converters, High Voltage Auxiliaries
- Solar Inverters, UPS, Digital Power Generator





Absolute Maximum Ratings

Symbol	Description		Ratings	Units	
V _{CES}	Collector to Emitter Voltage		650	V	
V _{GES}	Gate to Emitter Voltage		± 20	V	
I _C	Collector Current	@ T _C = 25°C	150	А	
	Collector Current	$@ T_C = 100^{\circ}C$	75	А	
I _{CM (1)}	Pulsed Collector Current		225	Α	
I _F	Diode Forward Current	@ T _C = 25°C	75	А	
	Diode Forward Current	$@ T_C = 100^{\circ}C$	50	Α	
I _{FM(1)}	Pulsed Diode Maximum Forward Current		225	А	
P _D	Maximum Power Dissipation	@ T _C = 25°C	375	W	
	Maximum Power Dissipation	@ T _C = 100°C	187	W	
SCWT	Short Circuit Withstand Time	@ T _C = 25°C	5	us	
T _J	Operating Junction Temperature		-55 to +175	°C	
T _{stg}	Storage Temperature Range		-55 to +175	°C	
T _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}(IGBT)_{(2)}$	Thermal Resistance, Junction to Case	0.4	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case	0.86	°C/W

Symbol	Parameter	Тур.	Units	
$R_{ heta JA}$	Thermal Resistance, Junction to Ambient (PCB Mount)(2)	40	°C/W	

Package Marking and Ordering Information

Device Marking	Device	Package	Packing Type	Qty per Tube
FGH75T65UPD	FGH75T65UPD_F085	TO-247	Tube	30ea

For Fairchild's definition of "green" Eco Status, please visit: http://www.fairchildsemi.com/company/green/rohs_green.html.

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Charac	teristics					
BV _{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0V$, $I_C = 1mA$	650	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_{J}}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V$, $I_C = 1mA$	-	0.65	-	V/°C
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	-	-	250	
		I _{CES} at 80%*B _{VCES} , 175°C	-	-	3600	μА
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	-	-	±400	nA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	$I_C = 75$ mA, $V_{CE} = V_{GE}$	4.0	6.0	7.5	V
02()		I _C = 75A, V _{GE} = 15V	_	1.69	2.3	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 75A, V _{GE} = 15V, T _C = 175°C	-	2.21	-	V
Dynamic C	haracteristics	1	II.	•	l	
C _{ies}	Input Capacitance		-	5665	-	pF
C _{oes}	Output Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$	_	205	-	pF
C _{res}	Reverse Transfer Capacitance	f = 1MHz	-	100	-	pF
	Characteristics	1	II.	•	l	
t _{d(on)}	Turn-On Delay Time		-	32	48	ns
t _r	Rise Time		-	43	71	ns
t _{d(off)}	Turn-Off Delay Time	V _{CC} = 400V, I _C = 75A,	-	166	216	ns
t _f	Fall Time	$R_G = 3\Omega$, $V_{GE} = 15V$,	-	24	33	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 25°C	-	2.85	4.80	mJ
E _{off}	Turn-Off Switching Loss		-	1.20	1.60	mJ
E _{ts}	Total Switching Loss		-	4.05	5.3	mJ
t _{d(on)}	Turn-On Delay Time		-	30	-	ns
t _r	Rise Time		-	57	-	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400V, I_{C} = 75A,$	-	176	-	ns
t _f	Fall Time	$R_G = 3\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 175^{\circ}C$	-	21	-	ns
E _{on}	Turn-On Switching Loss		-	4.45	-	mJ
E _{off}	Turn-Off Switching Loss		-	1.60	-	mJ
E _{ts}	Total Switching Loss		-	6.05	-	mJ
Tsc	Short Circuit Withstand Time	$V_{\rm GE} = 15 \text{V}, \ V_{\rm CC} \le 400 \text{V},$ Rg = 10 \Omega	5	-	-	us

Notes:

2:Rthjc for TO-247: according to Mil standard 883-1012 test method. Rthja for TO-247: according to JESD51-2, test method environmental condition and JESD51-10, test boards for through hole perimeter leaded package thermal measurements. JESD51-3: Low Effective Thermal Conductivity Test Board for Leaded Surface Mount Package.

^{1:}Repetitive rating: Pulse width limited by max junction temperature.

Electrical Characteristics of the IGBT (Continued)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Units
Q_g	Total Gate Charge		-	385	578	nC
Q _{ge}	Gate to Emitter Charge	$V_{CE} = 400V, I_{C} = 75A,$ $V_{GE} = 15V$	-	45	68	nC
Q_{gc}	Gate to Collector Charge	VGE - 10 V	-	210	315	nC

Electrical Characteristics of the Diode $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max	Units
V _{FM}	Diode Forward Voltage	I _F = 50A	$T_C = 25^{\circ}C$	-	2.1	2.6	V
FIVI	2.000 r omara romage		$T_{\rm C} = 175^{\rm o}{\rm C}$	-	1.7	-	1 1
E _{rec}	Reverse Recovery Energy		$T_{\rm C} = 175^{\rm o}{\rm C}$	-	40	-	uJ
t _{rr}	Diode Reverse Recovery Time	$I_{\rm F} = 50$ A, $dI_{\rm F}/dt = 200$ A/µs	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	43	85	ns
*IT	2.000 1.010.00 1.00010.9 1	ης -30Λ, αιρ/αι - 200Λ/μ3	$T_{\rm C} = 175^{\rm o}{\rm C}$	-	162	-	
Q _{rr}	Diode Reverse Recovery Charge		$T_C = 25^{\circ}C$	-	83	170	nC
~11	2.533 No. 3. 3. No. 3 No		$T_{\rm C} = 175^{\rm o}{\rm C}$	-	805	ı	

Figure 1. Typical Output Characteristics

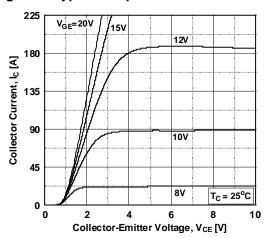


Figure 3. Typical Saturation Voltage Characteristics

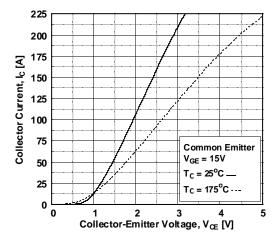


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level

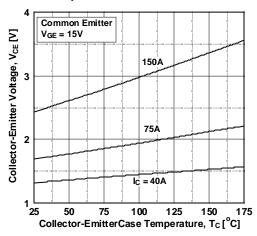


Figure 2. Typical Output Characteristics

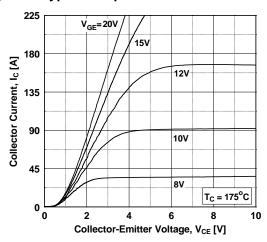


Figure 4. Transfer Characteristics

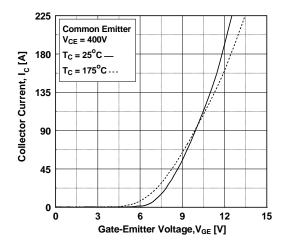


Figure 6. Saturation Voltage vs. V_{GE}

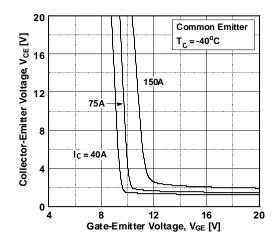


Figure 7. Saturation Voltage vs. V_{GE}

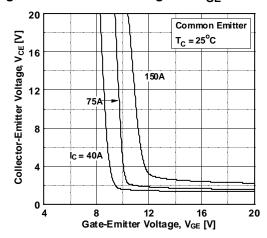


Figure 9. Capacitance Characteristics

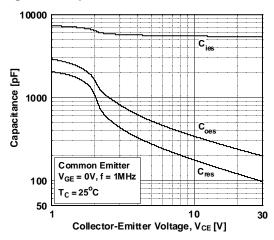


Figure 11. SOA Characteristics

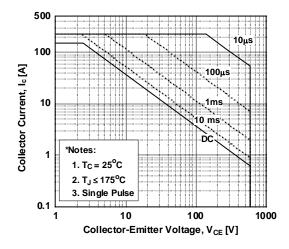


Figure 8. Saturation Voltage vs. V_{GE}

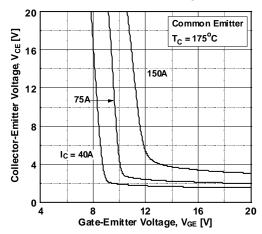


Figure 10. Gate charge Characteristics

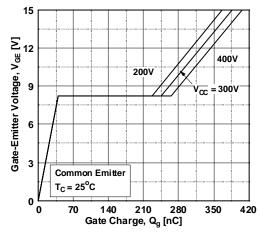


Figure 12. Turn-on Characteristics vs.
Gate Resistance

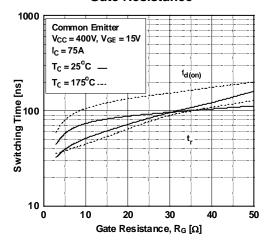


Figure 13. Turn-off Characteristics vs. Gate Resistance

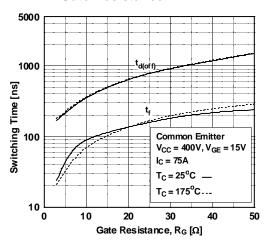


Figure 15. Turn-off Characteristics vs. Collector Current

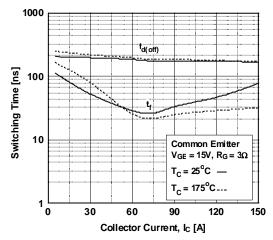


Figure 17. Switching Loss vs. Collector Current

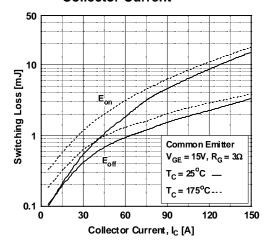


Figure 14. Turn-on Characteristics vs.
Collector Current

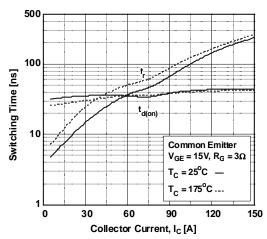


Figure 16. Switching Loss vs.
Gate Resistance

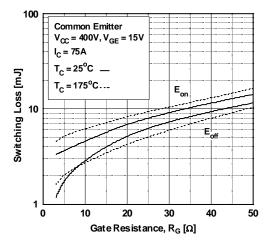


Figure 18. Turn off Switching SOA Characteristics

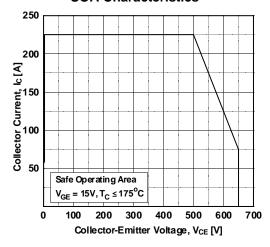


Figure 19. Current Derating

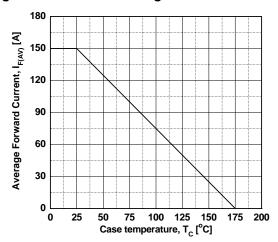


Figure 21. Forward Characteristics

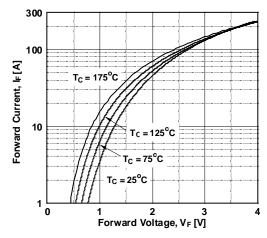


Figure 23. Stored Charge

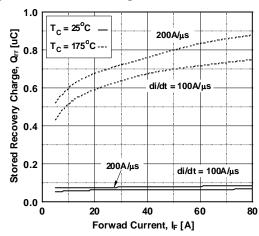


Figure 20. Load Current Vs. Frequence

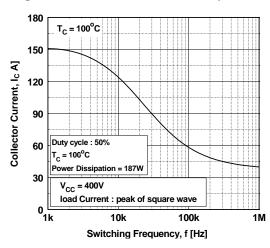


Figure 22. Reverse Recovery Current

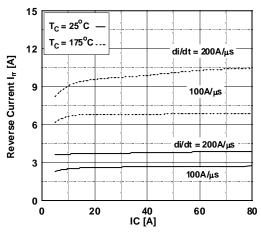


Figure 24. Reverse Recovery Time

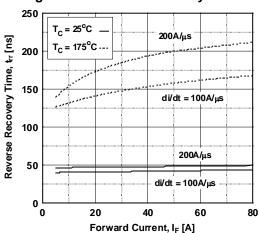


Figure 25. Transient Thermal Impedance of IGBT

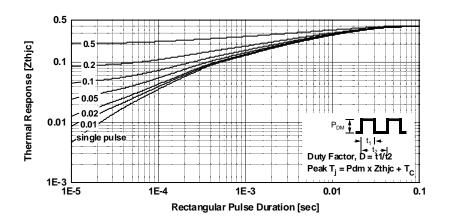
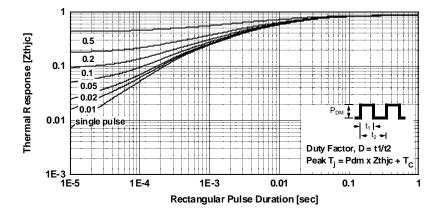
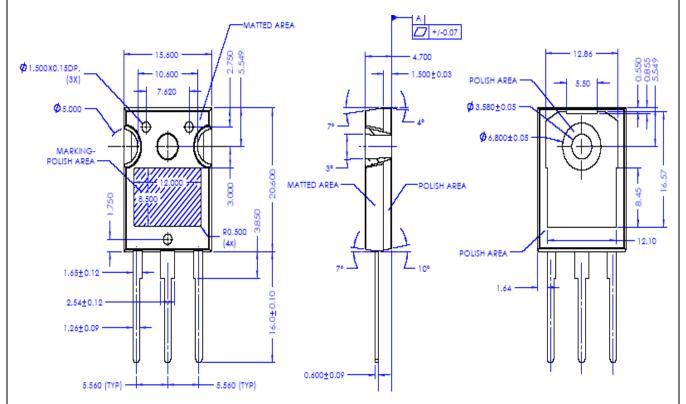


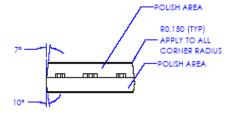
Figure 26.Transient Thermal Impedance of Diode



Mechanical Dimensions

TO - 247AB (FKS PKG CODE 001)









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